

isc Silicon NPN Power Transistor

2SC6082

DESCRIPTION

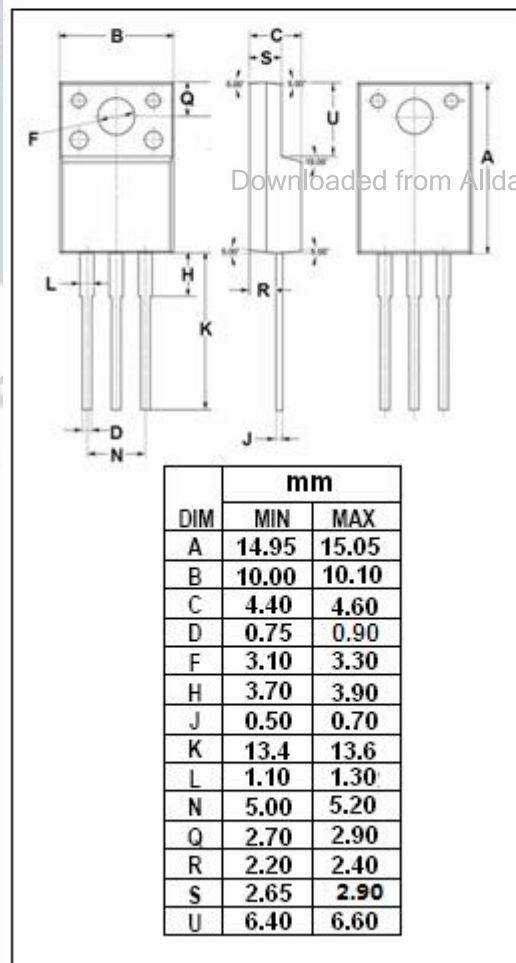
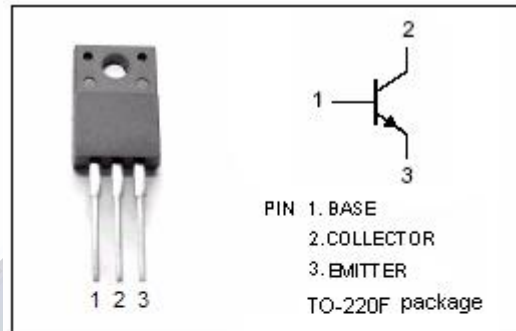
- Large current capacitance
- High speed switching
- Low saturation voltage
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- High speed switching applications

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current- Continuous	15	A
I _B	Base Current- Continuous	3	A
I _{CP}	Collector Current-Pulse	20	A
P _C	Collector Power Dissipation @ T _a =25°C	2	W
	Collector Power Dissipation @ T _c =25°C	23	
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



isc Silicon NPN Power Transistor**2SC6082****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 7.5A; I _B = 0.375A			0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 7.5A; I _B = 0.375A			1.2	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 40V; I _E = 0			10	μ A
h _{FE-1}	DC Current Gain	I _C = 330mA; V _{CE} = 2V	200		560	
h _{FE-2}	DC Current Gain	I _C = 10A; V _{CE} = 2V	50			
t _{stg}	Storage Time			560		ns
t _f	Fall Time	I _C = 5A, I _{B1} = 0.25A; I _{B2} = -0.25A		37		ns